2023 Virtual School on Many-Body Calculations using EPW and BerkeleyGW

Phonon-assisted optical absorption with EPW

Hands-on session (Tue.4)

Hands-on based on QE-v7.2 and EPW-v5.7

## Exercise

Before you start, please copy the tutorial tarball to your own scratch directory:

```
$ cp /work2/06868/giustino/SCHOOL/tutorials/Tue.4.Zhang.tar $SCRATCH
```

In this example we are going to calculate the phonon-assisted optical absorption spectrum of silicon. Extract the tarball Tue.4.Zhang.tar:

\$ tar -xvf Tue.4.Zhang.tar
\$ cd Tue.4.Zhang

You can find all inputs we will use in this tutorial as well as some output files for verification purposes in the results folder. For a complete list of inputs please follow the link:

https://epwdoc.gitlab.io/source/doc/Inputs.html

You are advised to prepare the following queue submission script:

```
#!/bin/bash
#SBATCH -J myjob # Job name
#SBATCH -o myjob.o%j # Name of stdout output file
#SBATCH -e myjob.e%j # Name of stderr error file
#SBATCH -N 1 # Total number of nodes
#SBATCH --ntasks-per-node 4
#SBATCH -t 00:10:00 # Run time (hh:mm:ss)
#SBATCH -A EPSchool2022
#SBATCH -p small # partition (development/normal/small)
#SBATCH --reservation=EPW-SCHOOL-Tue # reservation (must use current day)
QE=/work2/06868/giustino/SCHOOL/q-e-qe-7.2/bin
cd $PWD
```

Note: The path to the executables are set in the submission script. If you are using your own computer, remember to change the line to:

\$ export QE='PATH-TO-QE/q-e/bin'

▶ Make a self-consistent calculation for Si.

&control		scf.in
calculation	= 'scf'	
prefix	= 'si'	
restart_mode	= 'from_scratch'	

```
= './'
    pseudo_dir
                     = './'
    outdir
 1
&system
    ibrav
                     = 2
    celldm(1)
                     = 10.262
    nat
                     = 2
                     = 1
    ntyp
    ecutwfc
                     = 20
 1
&electrons
    diagonalization = 'david'
    mixing_beta
                    = 0.7
    conv_thr
                    = 1.0d-13
ATOMIC_SPECIES
 Si 28.0855 Si_r.upf
ATOMIC_POSITIONS alat
 Si 0.00 0.00 0.00
Si 0.25 0.25 0.25
K_POINTS automatic
12 12 12 0 0 0
```

**Note**: The k-point grid needs to be fairly dense in order to get converged dielectric function and Born effective charge during the following phonon calculation.

\$ ibrun -np 4 \$QE/pw.x < scf.in > scf.out

 $\triangleright$  Compute the vibrational properties of Si on a coarse  $3 \times 3 \times 3$  q-point grid.

\$ ibrun -np 56 \$QE/ph.x -nk 28 < ph.in > ph.out

The calculation should take about 1 min on 56 cores. During the run, notice the IBZ q-point grid (You can look at the output file or simply use the following command grep -6 Dynamical ph.out | tail -7):

```
Dynamical matrices for (3, 3, 3) uniform grid of q-points
(
 4 q-points):
 Ν
        xq(1)
                      xq(2)
                                    xq(3)
 1 0.00000000 0.00000000
                             0.00000000
 2 -0.33333333 0.333333333
                             -0.333333333
 3
     0.000000000
                 0.666666667
                               0.00000000
 4
     0.666666667 -0.00000000
                               0.666666667
```

as well as the dielectric function and Born effective charge tensor (You can look at the otput file or simply use the following command grep -15 'Dielectric constant in' ph.out | tail -17):

	Dielec	tric constant	in cartesian	sian axis		
	( 12.982914367 ( 0.000000000 ( -0.000000000 Effective charges (d		0.00000 12.98291 -0.00000	L4367 ·	0.000000000 ) -0.000000000 ) 12.982914367 )	
			d Force / dE)	in cartesia	an axis	
	atom	1 Si				
Ex	(	-0.00778	0.00000	0.000	( 000	
Ey	(	0.00000	-0.00778	-0.000	( 000	
Ez	(	0.00000	-0.00000	-0.00	778 )	
	atom	2 Si				

Ex	(	-0.00778	-0.00000	-0.00000 )
Ey	(	-0.00000	-0.00778	-0.00000 )
Ez	(	0.00000	-0.00000	-0.00778 )

The experimental dielectric constant of silicon is about 11.9 so that we overestimate it a bit. A smaller value can be obtained with larger k-point grids but DFT will always overestimate experiment. Since Si is a non polar material, the Born effective charges should be 0. Indeed, one can see that we are close to zero. In a converged calculation you may want to get an even smaller value.

► Like for the previous exercises, run the python post-processing to create the save folder (No job submission needed, can be ran simply on the login node.)

```
$ python3 $QE/../EPW/bin/pp.py
```

► Do a non self-consistent calculation on a homogeneous 6x6x6 **positively defined between 0 and** 1 **k**-point grid.

```
&control
                                                                                               nscf.in
                  = 'nscf'
   calculation
   prefix
                  = 'si'
   restart_mode
                  = 'from_scratch'
                  = './'
   pseudo_dir
                   = './'
   outdir
&svstem
   ibrav
                  = 2
   celldm(1)
                  = 10.262
                  = 2
   nat
                   = 1
   ntyp
                  = 20
   ecutwfc
                  = 12
   nbnd
&electrons
   diagonalization = 'david'
   mixing_beta = 0.7
                  = 1.0d-10
   conv_thr
ATOMIC_SPECIES
 Si 28.0855 Si_r.upf
ATOMIC_POSITIONS alat
 Si 0.00 0.00 0.00
 Si 0.25 0.25 0.25
K_POINTS crystal
216
 0.00000000 0.0000000 0.00000000 4.629630e-03
 0.00000000 0.0000000 0.166666667 4.629630e-03
```

\$ ibrun -np 4 \$QE/pw.x -npool 4 < nscf.in > nscf.out

▶ Perform an EPW calculation to interpolate the electron-phonon matrix element from a coarse 6x6x6 k and 3x3x3 q-point grids to real space and then interpolate the electronic and phononic bandstructure along the  $L - \Gamma - X$  high symmetry line.

```
--
&inputepw
prefix = 'si'
outdir = './'
elph = .true.
epbwrite = .true.
```

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epw1.in

```
epbread
           = .false.
epwwrite
          = .true.
           = .false.
epwread
etf_mem
           = 1
            = 8
nbndsub
eig_read.
          = .true.
           = 'crystal'
asr_typ
use_ws.
           = .true.
wannierize = .true.
num_iter = 1500
           = 2
iprint
dis_win_max = 18
dis_froz_max= 9
          = 'Si : sp3'
proj(1)
wdata(1) = 'bands_plot = .true.'
wdata(2) = 'begin kpoint_path'
wdata(3) = 'L 0.50 0.00 0.00 G 0.00 0.00 '
wdata(4) = 'G 0.00 0.00 0.00 X 0.50 0.50 0.00'
wdata(5) = 'end kpoint_path'
wdata(6) = 'bands_plot_format = gnuplot'
wdata(7) = 'guiding_centres = .true.'
wdata(8) = 'dis_num_iter = 500'
wdata(9) = 'num_print_cycles = 10'
wdata(10) = 'dis_mix_ratio = 1.0'
wdata(11) = 'use_ws_distance = T'
elecselfen = .false.
phonselfen = .false.
a2f
            = .false.
fsthick
           = 1.2 ! eV
           = 1 ! K
temps
          = 0.005 ! eV
degaussw
dvscf_dir = './save'
band_plot = .true.
           = './LGX.txt'
filkf
           = './LGX.txt'
filqf
            = 6
nk1
nk2
            = 6
nk3
            = 6
nq1
            = 3
            = 3
nq2
            = 3
nq3
1
```

\$ ibrun -np 56 \$QE/epw.x -npool 56 < epw1.in > epw1.out

The calculation should take about 1 min. In the output, notice the additional information related to the crystal ASR. At the end of the calculation, because of the keyword band\_plot = .true., the code will produce band.eig and phband.freq files that contains the electronic and phononic bandstructure along a path given by filkf and filqf. Note that the tag eig\_read = .true. asks the code to read in an external set of eigenvalues (see si.eig) that needs to be on the same set of k-points grid and number of bands as the nscf calculation. Here a set of GW eigenvalues calculated with BerkeleyGW are provided.

Note: An option exists to use QE generated interatomic forces in EPW with setting lifc = .true.. This is not recommended, and instead, the combination of lifc = .false.(default) and use\_ws = .true. to ensure construction of the correct Wigner-Seitz cell is always recommended for consistency. If you want to convert the band.eig and phband.freq files into a format readable by gnuplot, you can use the plotband.x tool by doing: (No job submission needed, can be ran simply on the login node.)

## \$ \$QE/plotband.x

to launch a command line interface for the file generation. Note that the second prompt will define the y-axis bounds. You should check that both bandstructure looks reasonable.

► Do a restart calculation (restarting from the si.epmatwp file) and compute the phonon-assisted absorption spectrum of silicon in the visible range.

The phonon-assisted optical absorption formalism is presented in J. Noffsinger *et al.*, *Phys. Rev Lett.* **108**, 167402 (2012), *Phys. Rev. B* **107**, 115207, (2023), and in the most recent EPW technical paper: H. Lee, et al., arXiv: 2302.08085. The code calculates the imaginary part of the dielectric function due to phonon-assisted optical transitions in the spectral region between the indirect and direct band gaps:

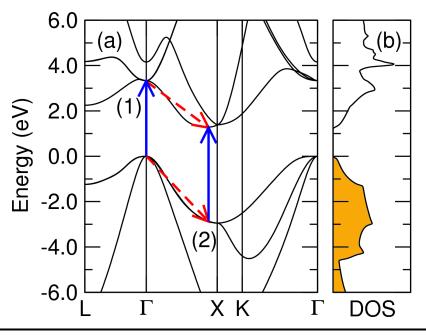
$$\begin{split} \mathsf{Im}[\epsilon(\omega)] &= 2 \frac{4\pi e^2}{\Omega} \frac{1}{\omega^2} \sum_{mn\nu,\beta=\pm 1} \int \frac{d\mathbf{k}}{\Omega_{\mathrm{BZ}}} \int \frac{d\mathbf{q}}{\Omega_{\mathrm{BZ}}} \left| \mathbf{e} \cdot \left[ \mathbf{S}_{1,mn\nu}(\mathbf{k},\mathbf{q}) + \mathbf{S}_{2,mn\nu\beta}(\mathbf{k},\mathbf{q}) \right] \right|^2 \\ &\times P_{mn\nu\beta}(\mathbf{k},\mathbf{q}) \delta(\varepsilon_{m\mathbf{k}+\mathbf{q}} - \varepsilon_{n\mathbf{k}} - \hbar\omega + \beta\hbar\omega_{\mathbf{q}\nu}), \end{split}$$
(1)

where  $\hbar\omega$  and e are the energy and polarization of the photon.  $\beta$  represent phonon absorption (-) or emission process (+). The generalized optical matrix elements,  $S_1$  and  $S_2$ , are given by

$$\mathbf{S}_{1,mn\nu}(\mathbf{k},\mathbf{q}) = \sum_{j} \frac{g_{mj\nu}(\mathbf{k},\mathbf{q})\mathbf{v}_{jn}(\mathbf{k})}{\varepsilon_{j\mathbf{k}} - \varepsilon_{n\mathbf{k}} - \hbar\omega + i\eta},$$
(2)

$$\mathbf{S}_{2,mn\nu\beta}(\mathbf{k},\mathbf{q}) = \sum_{j} \frac{\mathbf{v}_{mj}(\mathbf{k}+\mathbf{q})g_{jn\nu}(\mathbf{k},\mathbf{q})}{\varepsilon_{j\mathbf{k}+\mathbf{q}} - \varepsilon_{n\mathbf{k}} + \beta\hbar\omega_{\mathbf{q}\nu} + i\eta},$$
(3)

and correspond to the two possible paths of the indirect absorption process labelled (1) and (2) in the figure below:



They are determined in terms of the velocity  $(\mathbf{v})$  and electron-phonon coupling (g) matrix elements, as well as the quasiparticle energies  $(\epsilon_{n\mathbf{k}})$  and an imaginary broadening parameter  $(\eta)$ . The factor P accounts for the carrier and phonon statistics,

$$P_{mn\nu\beta}(\mathbf{k},\mathbf{q}) = \left(n_{\mathbf{q}\nu} + \frac{1+\beta}{2}\right) f_{n\mathbf{k}}(1 - f_{m\mathbf{k}+\mathbf{q}}) - \left(n_{\mathbf{q}\nu} + \frac{1-\beta}{2}\right) (1 - f_{n\mathbf{k}}) f_{m\mathbf{k}+\mathbf{q}}$$
(4)

The P factors can be obtained by considering energy conservation of the absorption/emission process.

The input file is as follows:

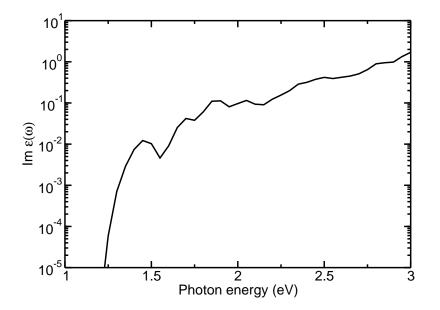
		epw2.in
&inputepw		
prefix	= 'si'	
outdir	= './'	
elph	= .true.	
epbwrite		
epbread		
epwwrite		
epwread	= .true. = 1	
etf_mem	= 1	
! band_plot	= .true.	
mp_mesh_k =		
lindabs = .		
efermi_read		
fermi_energ	-	
eig_read	true.	
omegamin =	0.05	
omegamax =		
omegastep =		
omegastep	0.00	
elecselfen	= .false.	
phonselfen		
a2f	= .false.	
fsthick	= 4.0 ! eV	
temps	= 300 ! K	
degaussw	= 0.05 ! eV	
dvscf_dir	= './save'	
nkf1	= 12	
nkf2	= 12	
nkf3	= 12	
nqf1	= 6	
nqf2	= 6	
nqf3	= 6	
nk1	= 6	
nkl nk2	= 6	
nk3	= 6	
nq1	= 3	
nq1 nq2	= 3	
nq3	= 3	
1-	-	
nbndsub	= 8	
use_ws	= .true.	
asr_typ	= 'crystal'	
wannierize	= .false.	
/		

## Notes:

- epwread allows for the restart from the si.epmatwp file.
- lindabs enables phonon-assisted optical absorption calculations.
- mp\_mesh\_k use only the irr. wedge for the fine electronic mesh. This reduces the computational cost significantly.
- omegamin, omegamax, omegastep are the minimum, maximum, and spacing of the photon energies for which we calculate the absorption coefficient.
- fermi\_energy = 5.57 sets the Fermi energy for silicon (insulator) in the middle of the gap, and fsthick = 4.0 limits the absorption calculation to states within an energy window around the Fermi level (set to be larger than the maximum photon energy we want the absorption spectra for plus the maximum phonon energy of the material).
- The code calculates the spectra with nine different broadening parameter values ( $\eta$  in the S-parameters, where  $\eta = 0.001, 0.002, 0.005, 0.01, 0.02, 0.05, 0.1, 0.2, 0.5 \text{ eV}$ ). Note that within the indirect region of the spectra, the choice of the broadening of the denominator does not affect the spectra significantly.

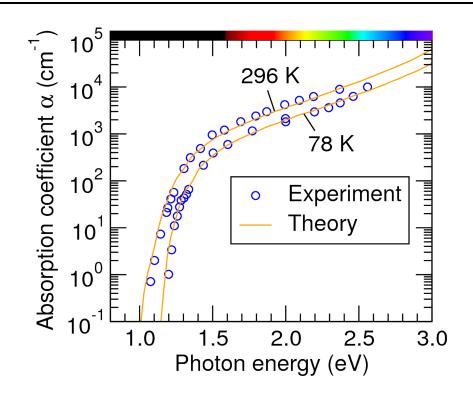
```
$ ibrun -np 56 $QE/epw.x -npool 56 < epw2.in > epw2.out
```

The run should take less than 1 min. You can find the directionally-averaged imaginary part of the phonon-assisted dielectric function for the different broadenings in epsilon2\_indabs\_300.0K.dat (Gaussian broadening for delta function) or epsilon2\_indabs\_lorenz300.0K.dat (Lorentzian broadening for delta function).<sup>1</sup> The first column is photon energy, while the other columns are the corresponding Im  $\epsilon(\omega)$  for different  $\eta$ s. The result should look like this (for the first  $\eta$  with Gaussian broadening for the delta function):



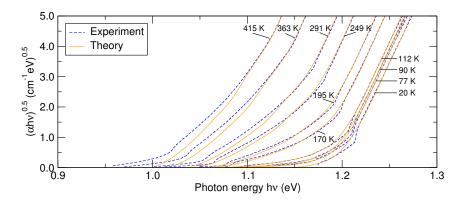
The fine **k** and **q** point grids need to be denser for production calculations. At convergence you should get a result similar to Fig. 3 of J. Noffsinger *et al.*, *Phys. Rev Lett.* **108**, 167402 (2012). Note that the relationship between Im  $\epsilon(\omega)$  and the absorption coefficient is  $\alpha(\omega) = \frac{\omega}{cn_r(\omega)} \text{Im } \epsilon(\omega)$ . The paper assumes a constant refractive index of  $n_r = 3.4$ .

 $<sup>^{1}</sup>$ Note that direct absorption within the independent particle approximation is also calcualted, see epsilon2\_dirabs\_300.0K.dat and epsilon2\_dirabs\_lorenz300.0K.dat. Careful convergence with respect to k-grid is important.



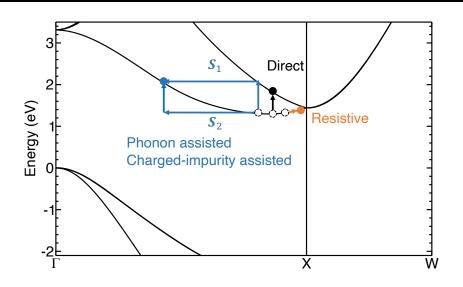
▶ Increase the fine grids to improve convergence.

You can also perform calculations to study the onset of phonon-assisted absorption and see the separate contributions from the phonon-absorption and the phonon-emission terms. These calculations need a small broadening parameter on the order of 10 meV (smaller than the phonon frequency) to distinguish the different onsets of the phonon-absorption and phonon-emission terms as well as fine  $\mathbf{k}$  and  $\mathbf{q}$  grids on the order of  $40 \times 40 \times 40$ . You can accelerate these calculations by selecting a narrow omegamin and omegamax range near the indirect absorption onset and adjusting the fsthick window accordingly. The converged result is similar to the spectra below from J. Noffsinger *et al.*, *Phys. Rev. Lett.* **108**, 167402 (2012):



► Free-carrier absorption (FCA)

In addition to the phonon-assisted optical absorption, you can add the combination of tags carrier and ncarrier to specify the carrier density in n-type (positive ncarrier) or p-type (negative ncarrier) semiconductors to study phonon-assisted free-carrier absorption. Free-carrier absorption occurs in doped semiconductors/metals when the conduction band minimum or valence band maximum is partially occupied/empty. Various mechanisms needs to be considered, as illustrated by Fig. 1 in *Phys. Rev. B* **106**, 205203:



The input for such a calculation is provided in epw3.in. Note that some of the previous output epsilon files in epw2 will be overridden.

			epw3.in
&inputepw			
omegamin			
omegamax	= 3.0		
omegaste			
	= .true.		
ncarrier	= 1e19		
ii_g = .			
ii_n = 1			
ii_lscre	en = .true.		
sigma_re	f = 16800		
	= 16		
nkf2			
nkf3			
nqf1	= 16		
nqf2	= 16		
nqf3	= 16		
1			

The following tags are relevant for free-carrier absorption:

- carrier: enable calculation of free-carrier absorption. The Fermi level will be determined by the carrier density.
- ncarrier: free-carrier density in cm<sup>-3</sup>, positive for free electrons and negative for free holes.
- ii\_g, ii\_n, ii\_lscreen: enables calculation of ionized-impurity assisted optics. See tutorial Mon.4
- sigma\_ref: conductivity of the material in  $\Omega^{-1} \cdot m^{-1}$ . Used to determine the resistive contribution within a constant relaxation time approximation:

Im 
$$\epsilon^{\text{resis}}(\omega) = \frac{4\pi\sigma}{\omega\left(1+\omega^2\tau^2\right)}$$
 (5)

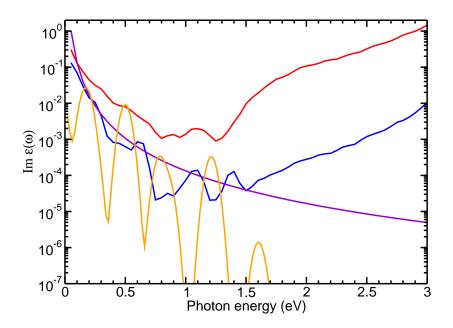
Note that the k- and q-points grid are finer in the input for this optional calculation. Since free-carrier absorption happens close to the conduction band minimum or valence band maximum, a much denser

grid is necessary to obtain converged result. In practice, similar to the case of mobility calculations, one can typically set fermi\_energy close to the conduction band minimum (for free electrons) or valence band maximum (for free holes), and use a smaller value of fsthick to reduce the computational cost due to that free-carrier absorption is dominant only in sub-gap region where photon energy is relatively small compared to cross-gap indirect absorption. Note that in this case, fermi\_energy is not used to set the Fermi-level used to calculate absorption, but only used to determine the states to consider according to fsthick.

Several outputs will be generated when free-carrier absorption is enabled:

- epsilon2\_indabs\_300.0K.dat: Phonon-assisted contribution.
- epsilon2\_indabs\_imp\_300.0K.dat: lonized-impurity-assisted contribution.
- epsilon2\_dirabs\_300.0K.dat, Direct contribution.
- epsilon2\_indabs\_resis\_300.0K.dat: Resistive contribution.

You may notice that the spectrum now has a strong dependence on the broadening  $\eta$  in Eq.(2) and Eq.(3), which is due to the divergence of the denominator. This divergence is present when direct transition (in this case, inter-conduction bands) is possible, and is a limitation of the second-order perturbation theory itself. It can be reduced by numerical approaches to cancel the diverging term, see e.g. Brown *et al.*, *ACS Nano*, **10.1**, 957-966 (2016). Plotting the phonon-assisted contribution (red) and ionized-impurity-assisted contribution (blue) with  $\eta = 0.1$  eV (column #8 in the files), direct contribution (orange) averaged over light polarization (last column), and the resistive contribution (purple), they should look like this:



You will notice the Im  $\epsilon(\omega)$  from all the contributions now contain sub-gap contributions that results from free-carrier absorption. In addition, one can see a severe underconvergence for all the contribution due to Brillouin zone sampling. In our previous study, a grid of  $48 \times 48 \times 48$  was required for converged free-carrier absorption spectra of silicon. More details about free-carrier absorption can be found at: *Phys. Rev. B* **106**, 205203. The converged result e.g. using a grid of  $48 \times 48 \times 48$ , is similar to Fig. 2 in the paper.

## Some tips for plotting

The output of the indirect optics module contains many multi-column data, with the first column being energy, the the other column being Im  $\epsilon(\omega)$  with different parameters. A few tips for visulizing the data using gnuplot:

• If you want to use gnuplot, you need to enable X-forwarding when logging in:

```
$ ssh your_account@frontera.tacc.utexas.edu -XC
```

• In the directory of your calculation, you can open gnuplot and plot a certain column of the data:

```
$ gnuplot
gnuplot> set logscale y
gnuplot> set yrange [1e-7:1]
gnuplot> plot "epsilon2_indabs_300.0K.dat" using 1:8 with lines
```

These commands set the y-axis to be log scale, and set the range to from  $10^{-7}$  to 1, and plot the 8th column ( $\eta = 0.1 \text{ eV}$ ) against the 1st column (Photon energy) with lines connecting the scattered data points.

• You can change the file name and use replot and plot another on top of the current plot, e.g., to plot the direct absorption, we plot the average (5th column):

gnuplot> replot "epsilon2\_dirabs\_300.0K.dat" using 1:5 with lines

• You can plot the different contributions with the above commands, and after you are done, you can exit gnuplot by typing

gnuplot> exit

Various other packages can be used to plot the data such as the matplotlib library in python, xmgrace. You can choose whichever you are more familiar with to visulize the data.